



DOCUMENT CHANGE REQUEST

DCR number	794	Changes required for:	General	Originator:	Samuel Savin
Date:	2013/09/30	Date sent:	2013/04/30	Organisation:	STMicroelectronics
Status:	IMPLEMENTED				

Title: TRANSISTORS, POWER, MOSFET, N-CHANNEL, RAD-HARD BASED ON TYPE STRH100N6

Number: 5205/022 Issue: 2

Other documents affected:

Page:

See document an attachment.

Paragraph:

See document an attachment.

Original wording:

See document an attachment.

Proposed wording:

See document an attachment.

Justification:

Test conditions have been reviewed according to new Drain Current (I_{DS} 40A) due to package performances and gate-oxide modified to 470 Å instead of 350Å.

Attachments:

strh100n6_dcr794_rev2.pdf, strh100n6_dcr.doc, null

Modifications:

The following additions and amendments to the original DCR attachment shall apply:

The original DCR attachment shall be replaced by strh100n6_dcr794_rev2. Only the following changes identified in this replacement attachment shall apply for this DCR:

Para 1.5

- Drain Current max ratings, I_{DS} , are amended
- Note 2, SOA figure is replaced

Para 2.5.1

- Forward Voltage ISD condition is amended (to be 40A; was 80A)
- Ciss, Coss, Crss limits are amended

- Qg, Qgs, Qgd limits and ID condition are amended
- td(on), tr, td(off), tf limits are amended
- trr limits and ISD condition are amended

Para 2.5.2

- Forward Voltage ISD condition is amended

Appendix A, Additional Data

Derating for Space Application text and SEESOA figure is replaced

Approval signature:

A handwritten signature in black ink, appearing to read "Andrew R. ...".

Date signed:

2013-09-30